

**INTRODUCE:**

HVGT high voltage silicon rectifier diodes is made of high quality Silicon chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

**FEATURES:**

1. High reliability design.
2. Low VF.
3. High frequency.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

**APPLICATIONS:**

1. High voltage multiplier circuit
2. General purpose high voltage rectifier.
3. Rectification for X-ray generator high voltage power supply.

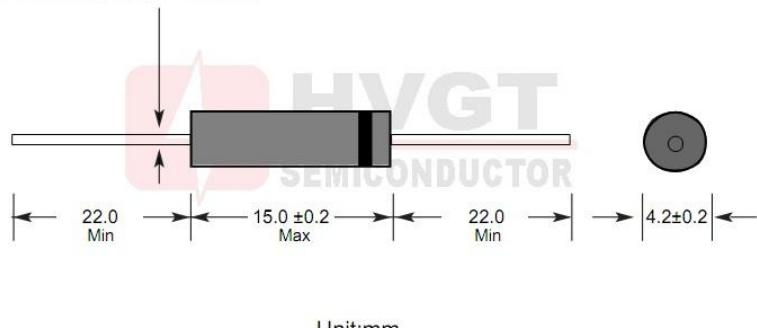
**MECHANICAL DATA:**

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.65 grams (approx).

**SHAPE DISPLAY:**

**SIZE: (Unit:mm)**
**HVGT NAME: DO-415**
**DO-415 Series**

Lead Diameter 0.8mm ±0.03



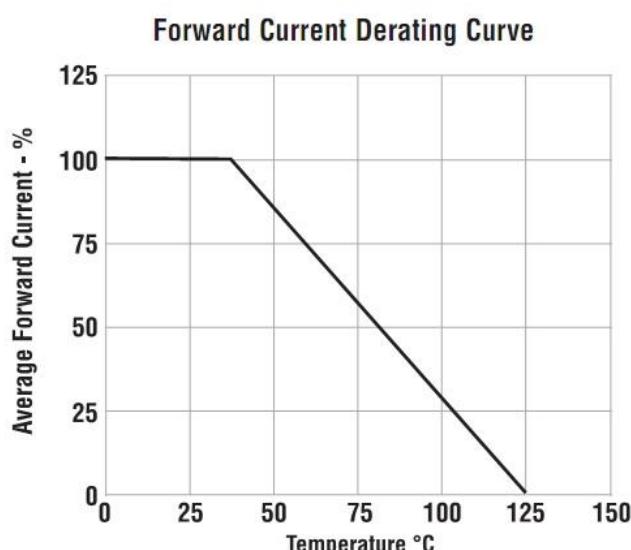
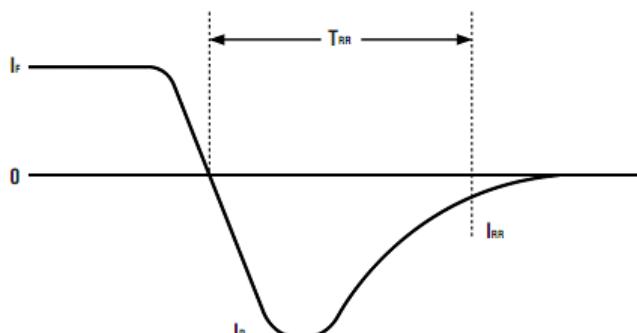
Unit:mm

**MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)**

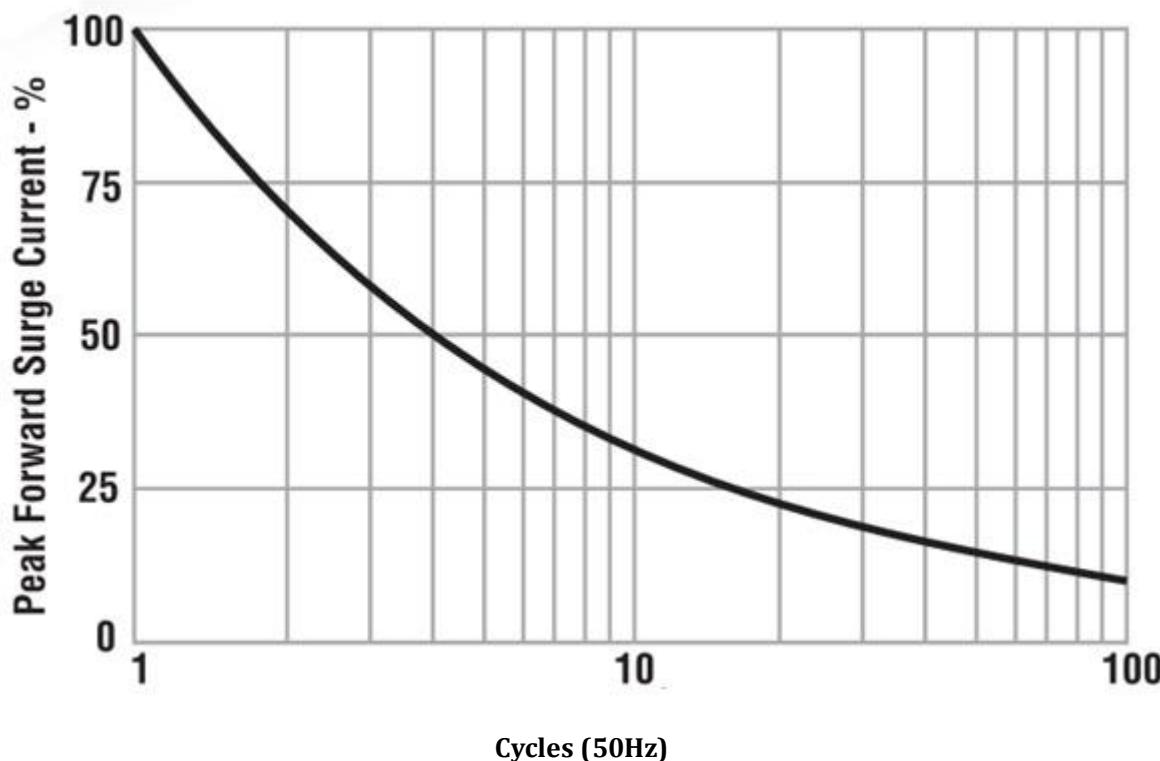
Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	T <sub>A</sub> =25°C	12	kV
Non-Repetitive Peak Reverse Voltage	V <sub>RSM</sub>	T <sub>A</sub> =25°C	--	kV
Average Forward Current Maximum	I <sub>FAVM</sub>	T <sub>A</sub> =40°C	300	mA
		T <sub>OIL</sub> =55°C	--	mA
Non-Repetitive Forward Surge Current	I <sub>FSM</sub>	T <sub>A</sub> =25°C; 50Hz Half-Sine Wave; 8.3mS	15	A
Junction Temperature	T <sub>J</sub>		125	°C
Allowable Operation Case Temperature	T <sub>c</sub>		-40~+125	°C
Storage Temperature	T <sub>STG</sub>		-40~+125	°C

**ELECTRICAL CHARACTERISTICS: T<sub>A</sub>=25°C (Unless Otherwise Specified)**

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V <sub>FM</sub>	at 25°C; at I <sub>FAVM</sub>	30	V
Maximum Reverse Current	I <sub>R1</sub>	at 25°C; at V <sub>RRM</sub>	2.0	uA
	I <sub>R2</sub>	at 100°C; at V <sub>RRM</sub>	10	uA
Maximum Reverse Recovery Time	T <sub>RR</sub>	at 25°C; I <sub>F</sub> =0.5I <sub>R</sub> ; I <sub>R</sub> =I <sub>FAVM</sub> ; I <sub>RR</sub> =0.25I <sub>R</sub>	100	nS
Junction Capacitance	C <sub>J</sub>	at 25°C; V <sub>R</sub> =0V; f=1MHz	15	pF

**Fig 1**
**Forward Current Derating Curve**

**Fig 2**
**Reverse Recovery Measurement Waveform**


Typical data capture points:  $I_F = 0.5I_R$ ,  $I_R, I_{RR} = 0.25I_R$   
 $I_R$  is typically the rated average forward current maximum ( $I_{FAVM}$ ) of the D.U.T

**Fig 3**
**Non-Repetitive Surge Current**

**Marking**
**Type**

ESJC37-12

**Code**

 ESJC37-12  
 HVGT

**Cathode Mark**
